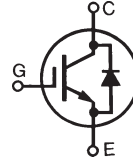




XPT™ 600V IGBTs GenX3™ w/ Diode

IXXK100N60B3H1 IXXX100N60B3H1

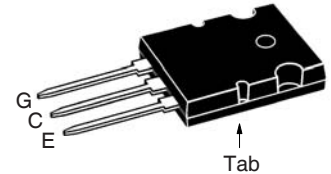
Extreme Light Punch Through
IGBT for 10-30kHz Switching



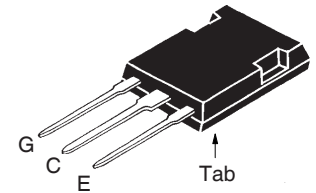
$$\begin{aligned} V_{CES} &= 600V \\ I_{C100} &= 100A \\ V_{CE(sat)} &\leq 1.80V \\ t_{fi(typ)} &= 150ns \end{aligned}$$

Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ\text{C}$ to 150°C	600	V
V_{CGR}	$T_J = 25^\circ\text{C}$ to 150°C , $R_{GE} = 1M\Omega$	600	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ\text{C}$ (Chip Capability)	200	A
I_{LRMS}	Terminal Current Limit	160	A
I_{C100}	$T_C = 100^\circ\text{C}$	100	A
I_{F110}	$T_C = 110^\circ\text{C}$	65	A
I_{CM}	$T_C = 25^\circ\text{C}$, 1ms	440	A
I_A	$T_C = 25^\circ\text{C}$	50	A
E_{AS}	$T_C = 25^\circ\text{C}$	600	mJ
SSOA (RBSOA)	$V_{GE} = 15V$, $T_{VJ} = 150^\circ\text{C}$, $R_G = 2\Omega$ Clamped Inductive Load	$I_{CM} = 200$ @ $V_{CE} \leq V_{CES}$	A
t_{sc} (SCSOA)	$V_{GE} = 15V$, $V_{CE} = 360V$, $T_J = 150^\circ\text{C}$ $R_G = 10\Omega$, Non Repetitive	10	μs
P_C	$T_C = 25^\circ\text{C}$	695	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
T_L	Maximum Lead Temperature for Soldering	300	$^\circ\text{C}$
T_{SOLD}	1.6 mm (0.062in.) from Case for 10s	260	$^\circ\text{C}$
M_d	Mounting Torque (TO-264)	1.13/10	Nm/lb.in.
F_C	Mounting Force (PLUS247)	20..120 /4.5..27	N/lb.
Weight	TO-264	10	g
	PLUS247	6	g

TO-264 (IXXK)



PLUS247 (IXXX)



G = Gate
C = Collector

E = Emitter
Tab = Collector

Features

- Optimized for 10-30kHz Switching
- Square RBSOA
- Avalanche Rated
- Short Circuit Capability
- Anti-Parallel Ultra Fast Diode
- High Current Handling Capability

Advantages

- High Power Density
- Low Gate Drive Requirement

Applications

- Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Battery Chargers
- Welding Machines
- Lamp Ballasts

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{CES}	$I_C = 250\mu\text{A}$, $V_{GE} = 0V$	600		V
$V_{GE(th)}$	$I_C = 250\mu\text{A}$, $V_{CE} = V_{GE}$	3.0		5.5 V
I_{CES}	$V_{CE} = V_{CES}$, $V_{GE} = 0V$ $T_J = 125^\circ\text{C}$			50 μA 4 mA
I_{GES}	$V_{CE} = 0V$, $V_{GE} = \pm 20V$			± 100 nA
$V_{CE(sat)}$	$I_C = 70A$, $V_{GE} = 15V$, Note 1 $T_J = 150^\circ\text{C}$		1.50 1.77	V V

Symbol Test Conditions

(T_J = 25°C Unless Otherwise Specified)

Characteristic Values

		Min.	Typ.	Max.
g_{fs}	I _C = 60A, V _{CE} = 10V, Note 1	22	40	S
C_{ies}	V _{CE} = 25V, V _{GE} = 0V, f = 1MHz		4860	pF
C_{oes}			475	pF
C_{res}			83	pF
Q_{g(on)}	I _C = 70A, V _{GE} = 15V, V _{CE} = 0.5 • V _{CES}		143	nC
Q_{ge}			37	nC
Q_{gc}			60	nC
t_{d(on)}	Inductive load, T _J = 25°C I _C = 70A, V _{GE} = 15V V _{CE} = 360V, R _G = 2Ω Note 2		30	ns
t_{ri}			70	ns
E_{on}			1.9	mJ
t_{d(off)}			120	ns
t_{fi}			150	ns
E_{off}			2.0	mJ
t_{d(on)}	Inductive load, T _J = 150°C I _C = 70A, V _{GE} = 15V V _{CE} = 360V, R _G = 2Ω Note 2		32	ns
t_{ri}			60	ns
E_{on}			2.3	mJ
t_{d(off)}			150	ns
t_{fi}			200	ns
E_{off}			2.8	mJ
R_{thJC}				0.18 °C/W
R_{thCS}		0.15		°C/W

Reverse Diode (FRED)

Symbol Test Conditions

(T_J = 25°C Unless Otherwise Specified)

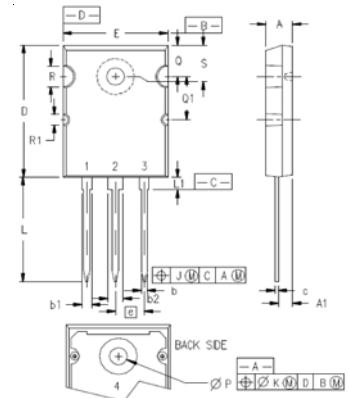
Characteristic Values

		Min.	Typ.	Max.
V_F	I _F = 60A, V _{GE} = 0V, Note 1		1.6	2.5 V
	T _J = 150°C		1.4	1.8 V
I_{RM}	I _F = 60A, V _{GE} = 0V, -di _F /dt = 200A/μs, V _R = 300V		8.3	A
t_{rr}			140	ns
R_{thJC}				0.30 °C/W

Notes:

1. Pulse test, t ≤ 300μs, duty cycle, d ≤ 2%.
2. Switching times & energy losses may increase for higher V_{CE}(clamp), T_J or R_G.

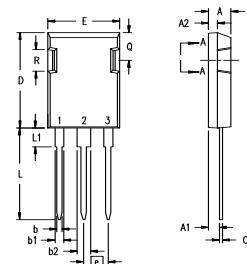
TO-264 Outline



Terminals: 1 = Gate
2,4 = Collector
3 = Emitter

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.185	.209	4.70	5.31
A1	.102	.118	2.59	3.00
b	.037	.055	0.94	1.40
b1	.087	.102	2.21	2.59
b2	.110	.126	2.79	3.20
c	.017	.029	0.43	0.74
D	1.007	1.047	25.58	26.59
E	.760	.799	19.30	20.29
e	.215 BSC		5.46 BSC	
J	.000	.010	0.00	0.25
K	.000	.010	0.00	0.25
L	.779	.842	19.79	21.39
L1	.087	.102	2.21	2.59
ØP	.122	.138	3.10	3.51
Q	.240	.256	6.10	6.50
Q1	.330	.346	8.38	8.79
ØR	.155	.187	3.94	4.75
ØR1	.085	.093	2.16	2.36
S	.243	.253	6.17	6.43

PLUS247™ Outline



Terminals: 1 - Gate
2 - Collector
3 - Emitter

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.83	5.21	.190	.205
A ₁	2.29	2.54	.090	.100
A ₂	1.91	2.16	.075	.085
b	1.14	1.40	.045	.055
b ₁	1.91	2.13	.075	.084
b ₂	2.92	3.12	.115	.123
C	0.61	0.80	.024	.031
D	20.80	21.34	.819	.840
E	15.75	16.13	.620	.635
e	5.45 BSC		.215 BSC	
L	19.81	20.32	.780	.800
L1	3.81	4.32	.150	.170
Q	5.59	6.20	.220	0.244
R	4.32	4.83	.170	.190

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered 4,835,592 4,931,844 5,049,961 5,237,481 6,162,665 6,404,065 B1 6,683,344 6,727,585 7,005,734 B2 7,157,338B2
by one or more of the following U.S. patents: 4,860,072 5,017,508 5,063,307 5,381,025 6,259,123 B1 6,534,343 6,710,405 B2 6,759,692 7,063,975 B2
4,881,106 5,034,796 5,187,117 5,486,715 6,306,728 B1 6,583,505 6,710,463 6,771,478 B2 7,071,537

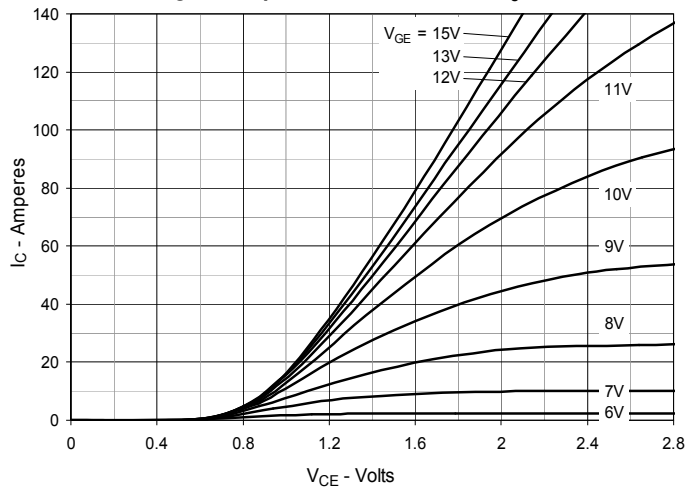
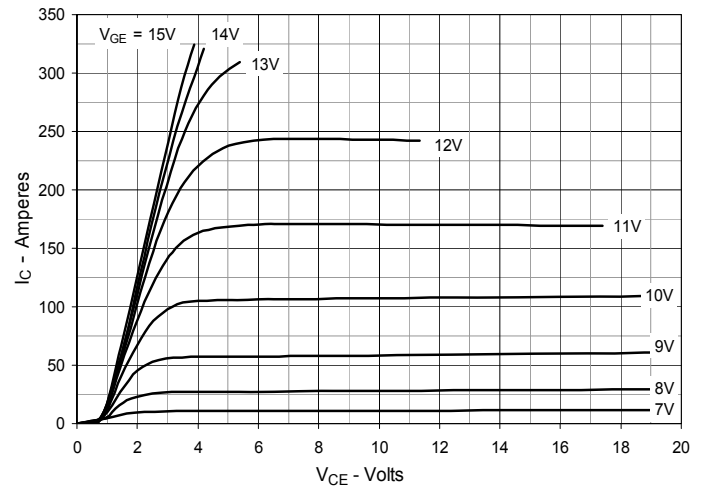
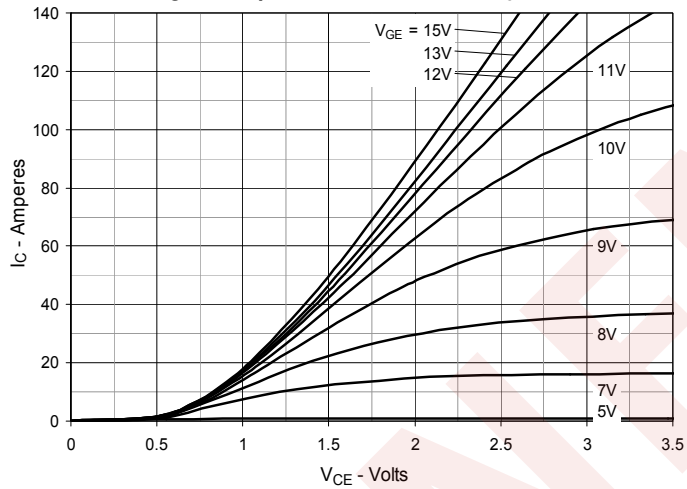
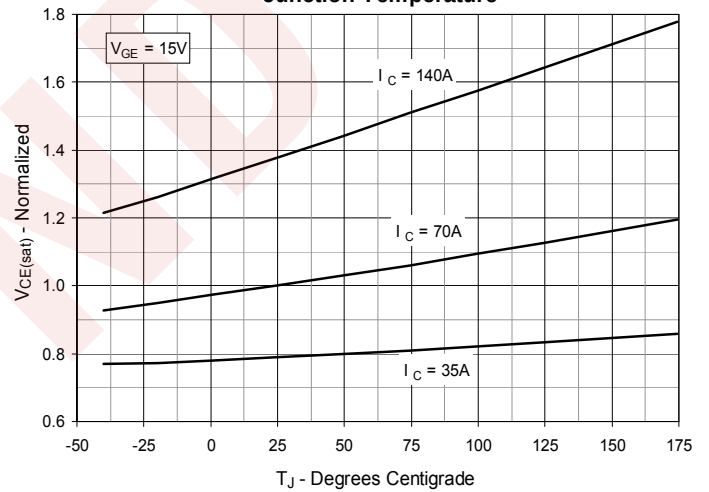
Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$ Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$ Fig. 3. Output Characteristics @ $T_J = 150^\circ\text{C}$ Fig. 4. Dependence of $V_{CE(sat)}$ on Junction Temperature

Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

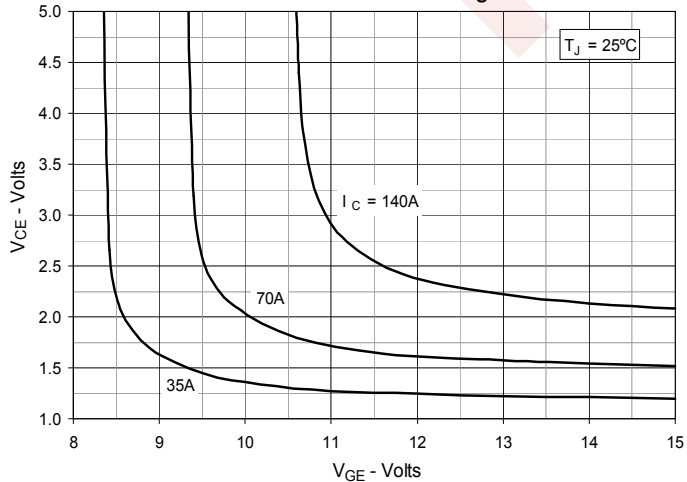


Fig. 6. Input Admittance

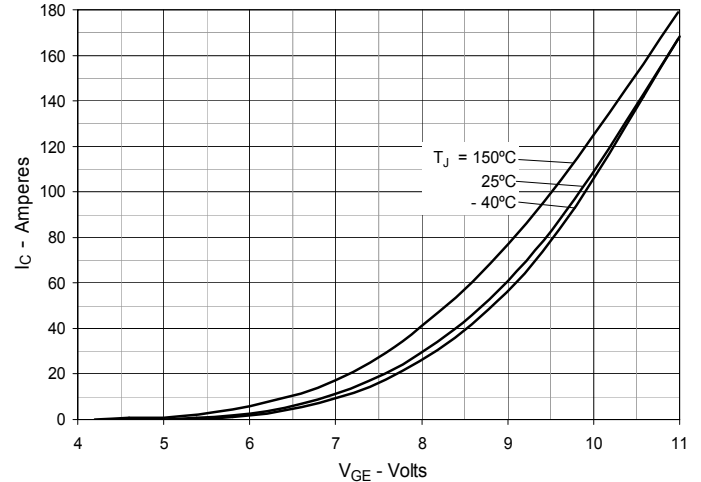


Fig. 7. Transconductance

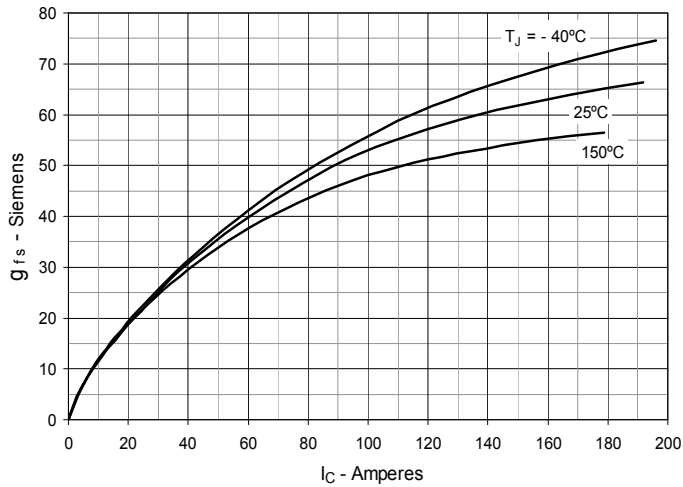


Fig. 8. Gate Charge

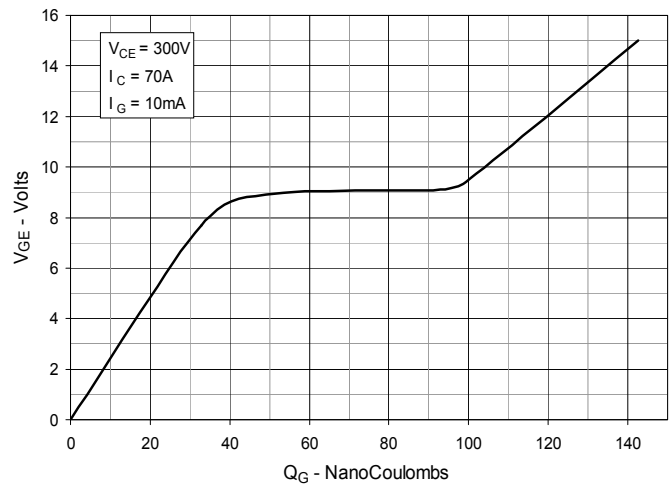


Fig. 9. Capacitance

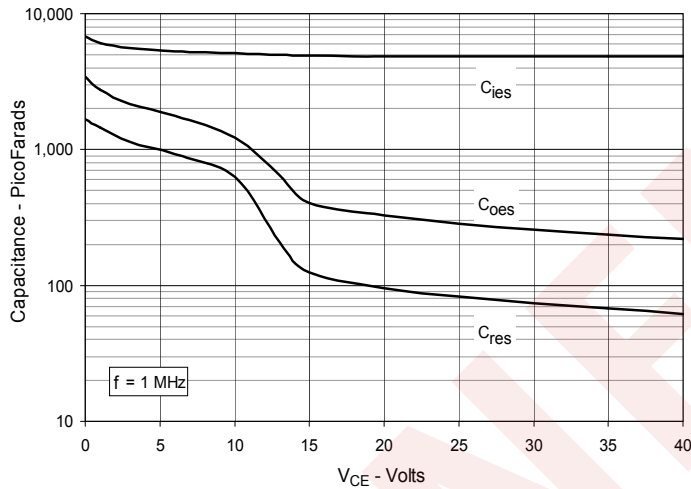


Fig. 10. Reverse-Bias Safe Operating Area

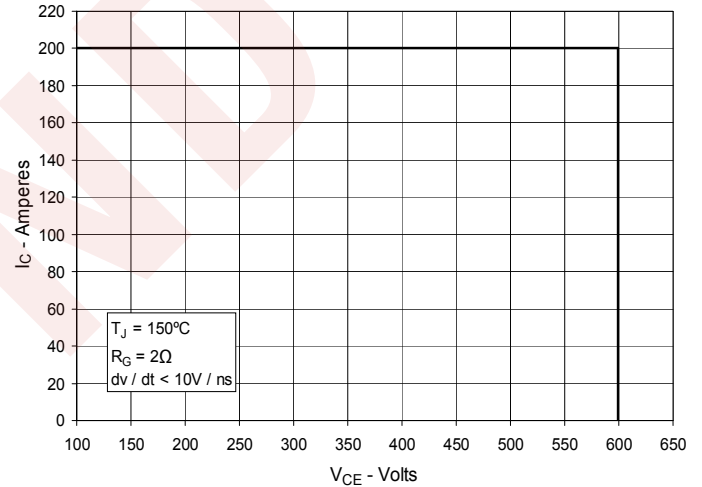


Fig. 11. Forward-Bias Safe Operating Area

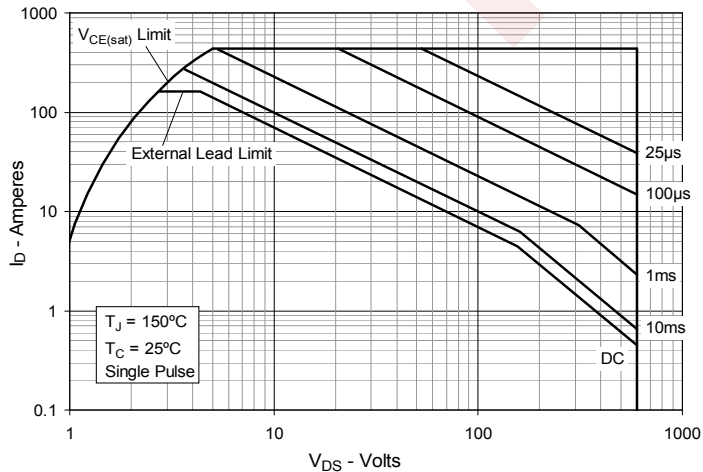


Fig. 12. Maximum Transient Thermal Impedance

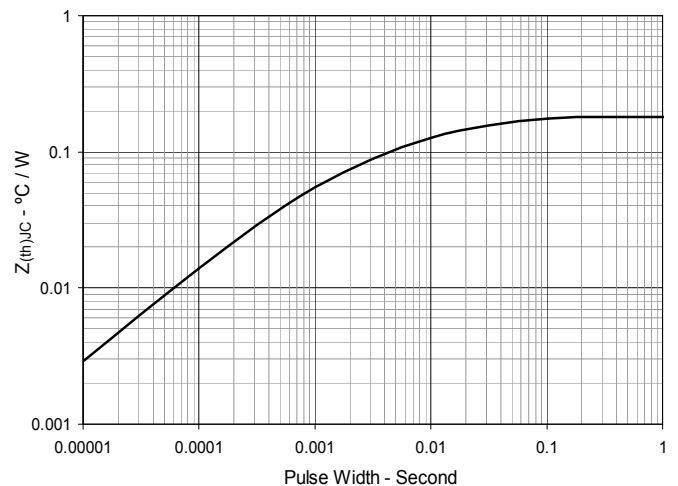


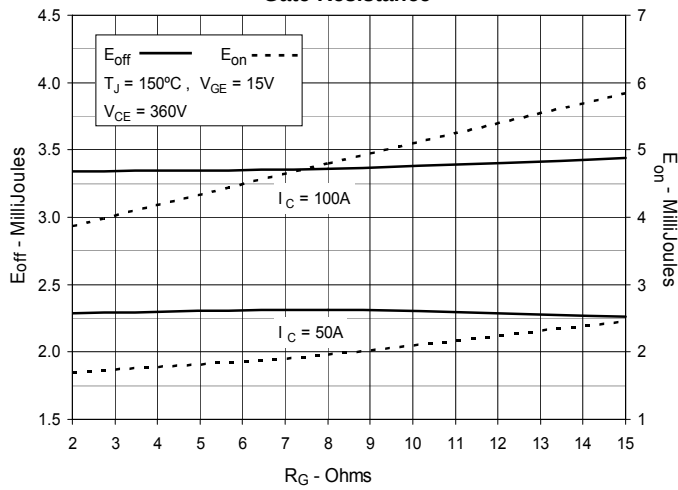
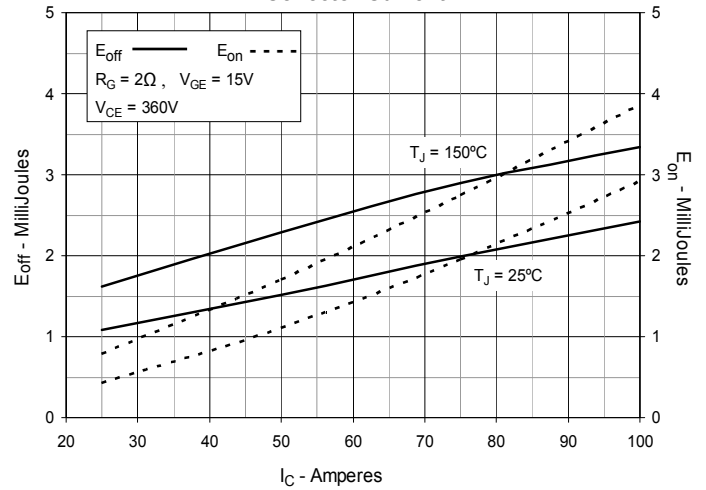
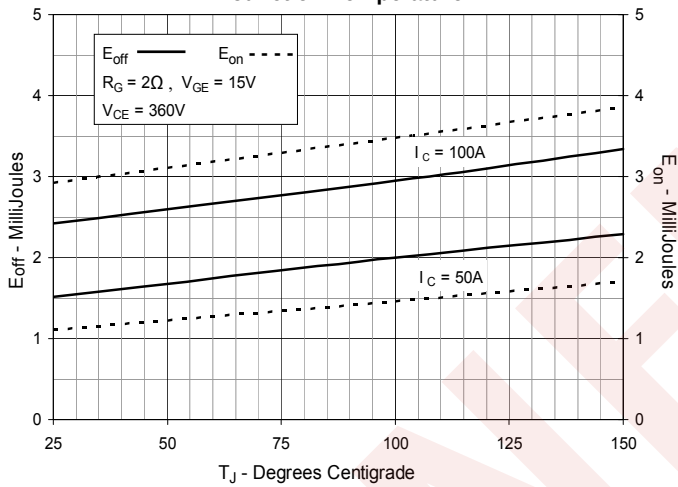
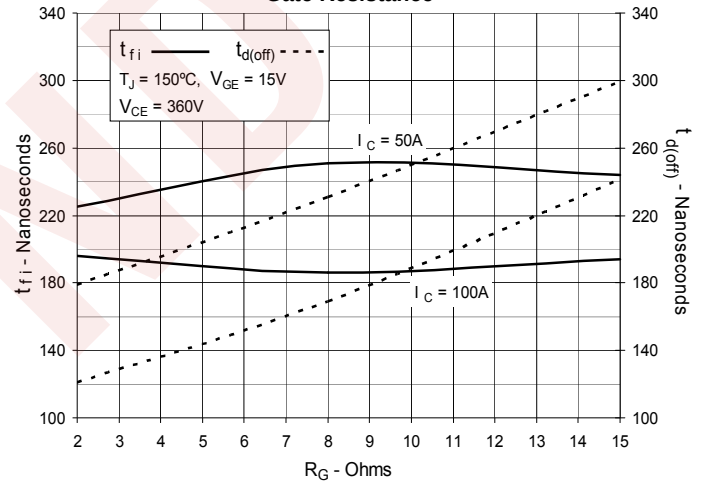
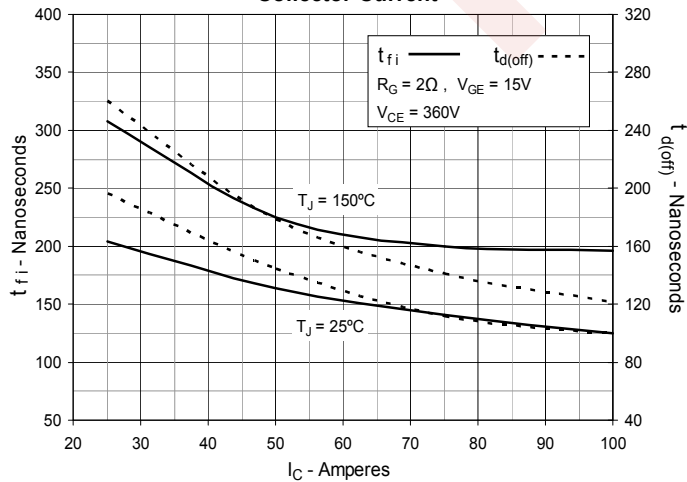
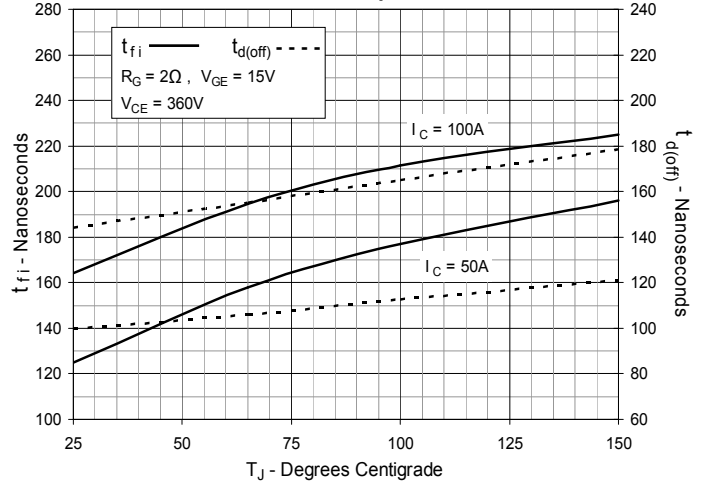
Fig. 13. Inductive Switching Energy Loss vs.
Gate ResistanceFig. 14. Inductive Switching Energy Loss vs.
Collector CurrentFig. 15. Inductive Switching Energy Loss vs.
Junction TemperatureFig. 16. Inductive Turn-off Switching Times vs.
Gate ResistanceFig. 17. Inductive Turn-off Switching Times vs.
Collector CurrentFig. 18. Inductive Turn-off Switching Times vs.
Junction Temperature

Fig. 19. Inductive Turn-on Switching Times vs. Gate Resistance

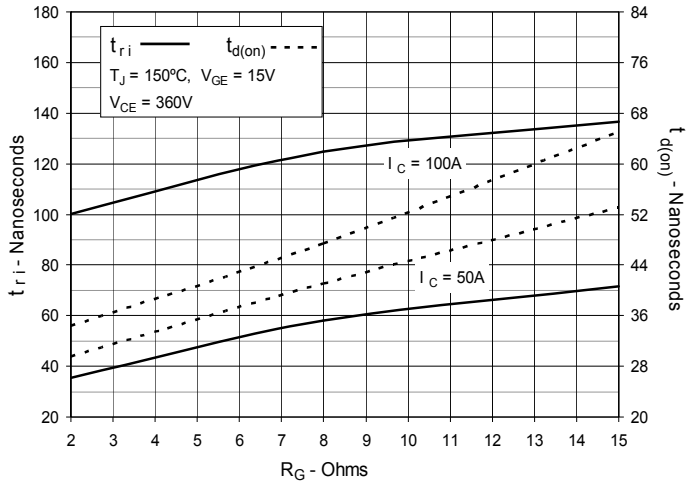


Fig. 20. Inductive Turn-on Switching Times vs. Collector Current

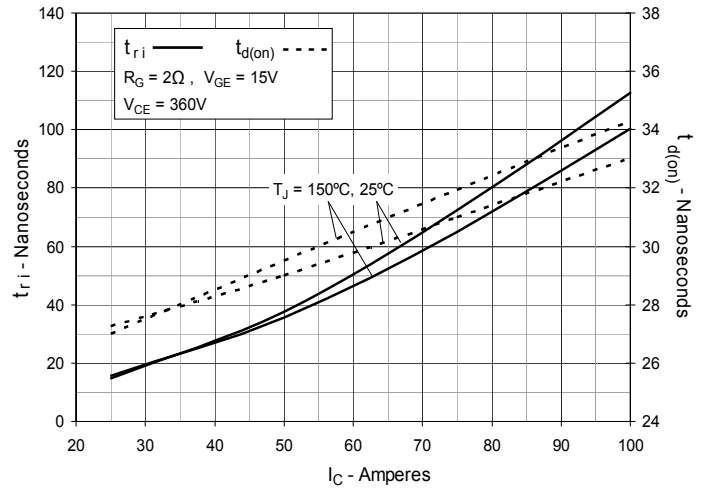
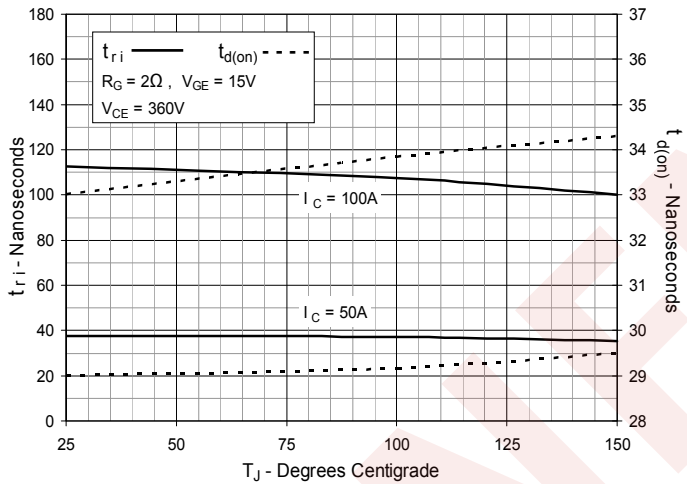


Fig. 21. Inductive Turn-on Switching Times vs. Junction Temperature



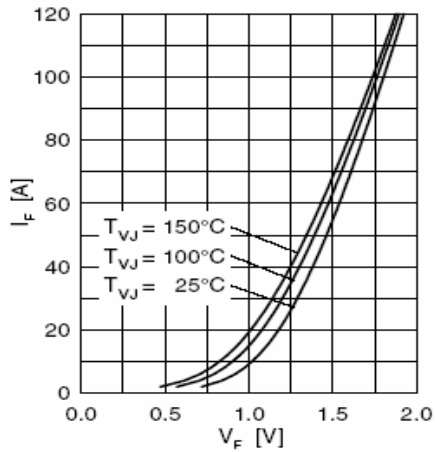
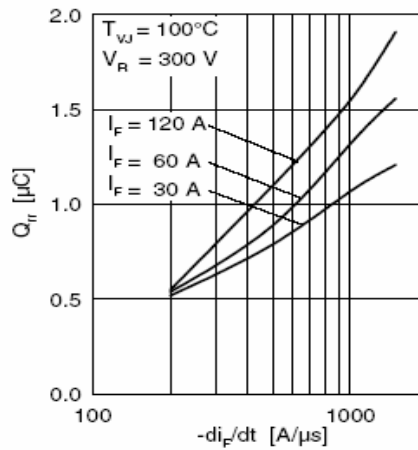
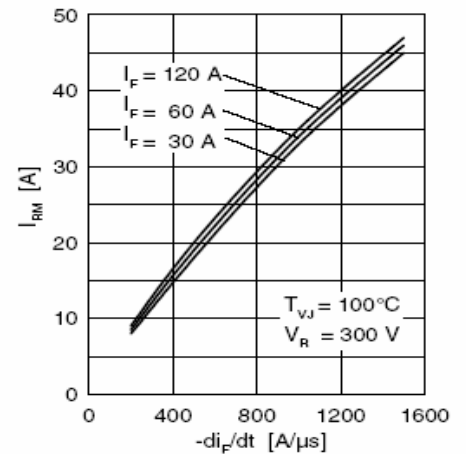
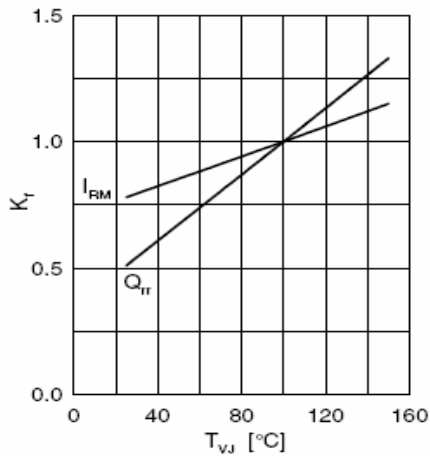
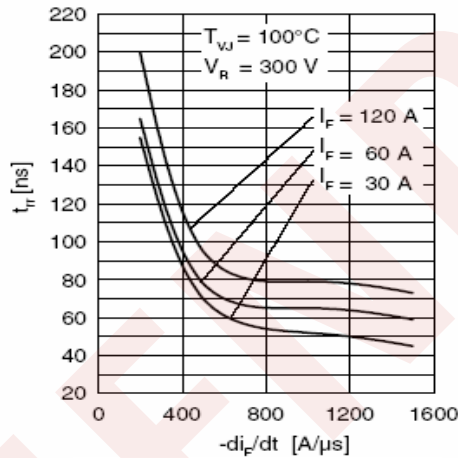
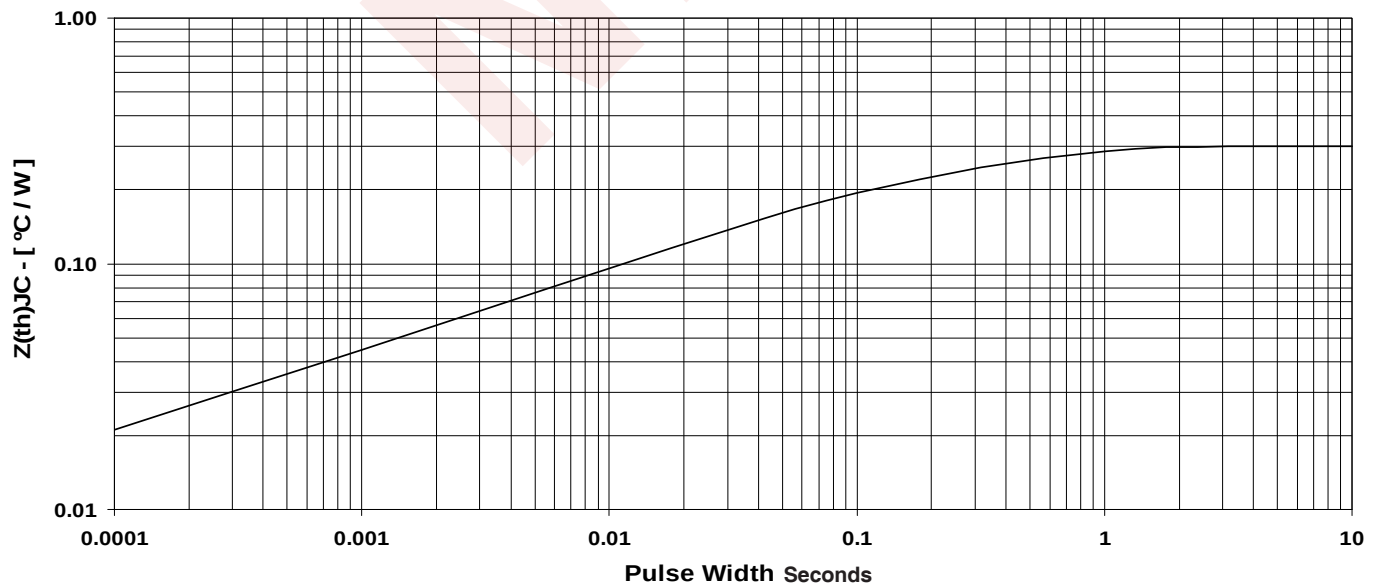
Fig. 22. Forward Current I_F Versus V_F Fig. 23. Reverse Recovery Charge Q_{rr} Versus $-di_F/dt$ Fig. 24. Peak Reverse Current I_{RM} Versus $-di_F/dt$ Fig. 25. Dynamic Parameters Q_{rr} , I_{RM} Versus T_{VJ} Fig. 26. Recovery Time t_{rr} Versus $-di_F/dt$ 

Fig. 27. Maximum transient thermal impedance junction to case (for diode)

NOT FOR NEW DESIGN

NEW



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